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3 A LOW Vf Schottky Barrier Rectifier

DESCRIPTION

This UPS340e3 in the Powermite3[®] package is a high efficiency Schottky rectifier that is also RoHS compliant offering high current/power capabilities previously found only in much larger packages. They are ideal for SMD applications that operate at high frequencies. In addition to its size advantages, the Powermite3[®] package includes a full metallic bottom that eliminates the possibility of solder flux entrapment during assembly and a unique locking tab act as an efficient heat path to the heat-sink mounting. Its innovative design makes this device ideal for use with automatic insertion equipment.

KEY FEATURES

- Very low thermal resistance package
- RoHS Compliant with e3 suffix part number
- Guard-ring-die construction for transient protection
- Efficient heat path with Integral locking bottom metal tab
- Low forward voltage
- Full metallic bottom eliminates flux entrapment
- Compatible with automatic insertion
- Low profile-maximum height of 1mm

IMPORTANT: For the most current data, consult *MICROSEMI*'s website: http://www.microsemi.com

ABSOLUTE MAXIMUM RATINGS AT 25 ^o C (UNLESS OTHERWISE SPECIFIED)					
Rating	Symbol	Value	Unit		
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	40	V		
RMS Reverse Voltage	V _{R (RMS)}	28	V		
Average Rectified Output Current	Ιo	3	А		
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine wave Superimposed on Rated Load@ T _c =90 °C	I _{FSM}	50	A		
Storage Temperature	T _{STG}	-55 to +150	°C		
Junction Temperature	TJ	-55 to +125	°C		

THERMAL CHARACTERISTICS

Thermal Resistance			
Junction-to-case (bottom)	R _{θJC}	3.2	°C/ Watt
Junction to ambient (1)	R _{0JA}	65	°C/ Watt
(1) When mounted on FR-4 PC board using 2 oz copper with recommended minimum foot print			

Powermite 3[™]



APPLICATIONS/BENEFITS
Switching and Regulating Power Supplies
Silicon Schottky (hot carrier) rectifier for
minimal reverse voltage recovery
Elimination of reverse-recovery oscillation

- everse-recovery oscillations to reduce need for EMI filtering
- Charge Pump Circuits
- Reduces reverse recovery loss with low I_{RM} =



190 X 270 mils (1:1 Actual size) See mounting pad details on pg 3

MECHANICAL & PACKAGING

- CASE: Void-free transfer molded thermosetting epoxy compound meeting UL94V-0
- FINISH: Annealed matte-Tin plating over copper and readily solderable per MIL-STD-750 method 2026 (consult factory for Tin-Lead plating)
- POLARITY: See figure (left)
- MARKING: S340•
- WEIGHT: 0.072 gram (approx.)
- Package dimension on last page
- Tape & Reel option: 16 mm tape per Standard EIA-481-B, 5000 on 13" reel



3 A LOW Vf Schottky Barrier Rectifier

ELECTRICAL PARAMETERS @25°C (unless otherwise specified)						
Parameter	Symbol	Conditions	Min	Тур.	Max	Units
		1			1	1
Forward Voltage (Note 1)		I _F = 3 A , T _j =25 °C		0.46	0.50	
	V	I _F = 3 A , T _i =125 °C		0.40	0.44	V
	VF	I _F = 6 A , T _i =25 °C		0.57	0.61	v
		I _F = 6 A , T _i =125 °C		0.54	0.58	
Reverse Break Down Voltage						
(Note 1)	V_{BR}	I _R = 0.5 mA	40			V
Reverse Current (Note1)		V _R = 40V, T _i = 25 °C		15	500	uA
	I _R	$V_{\rm R} = 40V, T_{\rm j} = 100 {}^{\circ}{\rm C}$		10	20	mA
Capacitance	CT	$V_R = 4 V; f = 1 MH_Z$		180		pF

Note: 1 Short duration test pulse used to minimize self - heating effect.



UPS340e3



3 A LOW Vf Schottky Barrier Rectifier



- Notes: 1. $T_A = T_{SOLDERING POINT}$, $R_{\Theta JS} = 3.2^{\circ} \text{ C/W}$ $R_{\Theta SA} = 0^{\circ} \text{ C/W}$. 2. Device mounted on GETEK substrate, 2" x 2", 2 oz. copper, double-sided, cathode pad dimensions 0.75" x 1.0", anode pad dimensions 0.25" x 1.0". R_{OJA} in range of 20-40° C/W.
 - 3. Device mounted on FRA-4 substrate, 2" x 2", 2 oz. copper, single-sided, pad layout $R_{\Theta JA}$ in range of 65° C/W. See mounting pad below.

MOUNTING PAD DIMENSIONS (inches)





3 A LOW Vf Schottky Barrier Rectifier

TAPE & REEL



13 INCH REEL





3 A LOW Vf Schottky Barrier Rectifier

PACKAGE DIMENSIONS





POWERMITE®3			
Dim	Min	Max	
•	4.03	4.09	
B	6.40	6.61	
С	.889 NOM		
D	1.83 NOM		
E	1.10	1.14	
G	.178 NOM		
Н	5.01	5.17	
J	4.37	4.43	
К	.178 NOM		
L	.71	.77	
M	.36	.46	
Р	1.73	1.83	
All Dimensions in mm			



3 A LOW Vf Schottky Barrier Rectifier

NOTES:	×
	vw.M
	icrose
	mi.co
	Z
NO	UPS34
TES	10e3

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